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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	NEW 10/758,009
				Filing Date	January 7, 2004 01/16/04
				First Named Inventor	Jiutao Li
				Art Unit	N/A 2815
				Examiner Name	Not Yet Assigned Featy
Sheet	1	of	9	Attorney Docket Number	M4065.0609/P609/P609-D

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	AA	5,761,115*	06/02/1998	Kozicki et al.	
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		Country Code ³	Number ⁴ -Kind Code ⁵ (if known)			
	BA	WO	02/21542*	03/14/2002	Kozicki et al.	
	BB	WO	00/48196*	08/17/2000	Kozicki et al.	
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
Examiner Signature	<i>Paul L. Fenty</i>	Date Considered	3/17/5
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se75Ge25-xSbx, Appl. Phys. A 55 (1992) 167-169.	
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	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
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	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
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	CO	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.	
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		Examiner Name	Not Yet Assigned Fenty		
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		First Named Inventor	Jiutao Li
		Group Art Unit	N/A 2815
		Examiner Name	Not Yet Assigned i-r-ty
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		Group Art Unit	N/A 2815
		Examiner Name	Not Yet Assigned Fein
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Examiner Signature	Not Yet Assigned Fein	Date Considered	3/17/05
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			First Named Inventor	Li Jiutao	
			Art Unit	2814 2815	
			Examiner Name	Not Yet Assigned Fenty	
Sheet	1	of	4	Attorney Docket Number	M4065.0609/P609-D

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
[Handwritten Initials]	**AA	2002/0132417	09/09/2002	Li	[Large diagonal line across the table]
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			Application Number	10/758,009	
			Filing Date	January 16, 2004	
			First Named Inventor	Li Jiutao	
			Art Unit	2811 3815	
			Examiner Name	Not Yet Assigned <i>Ferty</i>	
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